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FORM PTO-1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	ATTY. DOCKET NO. 2036/US/2 (1959/US/2)	APPLN. NO. 10/728,522
	APPLICANT: Romain Desplats et al.	
	FILING DATE December 5, 2003	GROUP 2829

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EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RL		Re. 33,241	06/1990	Tsuchiya	356	318	
		4,091,277	05/1978	Doblhofer	250	214 R	
		4,115,694	09/1978	Lange et al.	250	363 S	
		4,242,635	12/1980	Burns	324	158 R	
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		4,431,914	02/1984	Mourou et al.	250	211 J	
		4,555,731	11/1985	Zinchuk	358	209	
		4,591,984	05/1986	Mori	364	414	
		4,680,635	07/1987	Khurana	358	211	
		4,686,371	08/1987	Birch et al.	250	461.1	
		4,704,522	11/1987	Hirai et al.	250	213 VT	
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		4,755,874	07/1988	Esrig et al.	358	106	
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RK		**6,327,394	02/2001	Kash et al.	382	280	
RK		6,469,529	10/2002	Bruce et al.	324	752	
RK		*6,515,304	02/2003	Kash et al.	257	79	
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FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

		DOCUMENT NUMBER	PUBLISHED DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

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EXAMINER		DATE CONSIDERED	9-22-04

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*Cited in an International Search Report dated April 29, 2004 in corresponding International Application No. PCT/US03/38616.
**Cited in an International Search Report dated April 19, 2004 in related International Application No. PCT/US03/27267.